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Update on the APC Nb₃Sn project

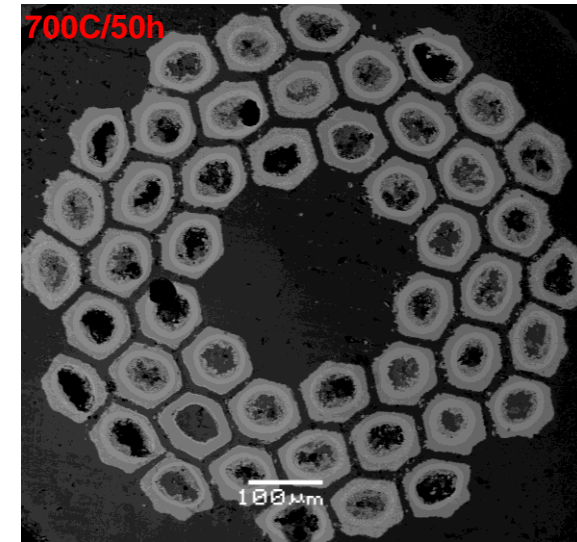
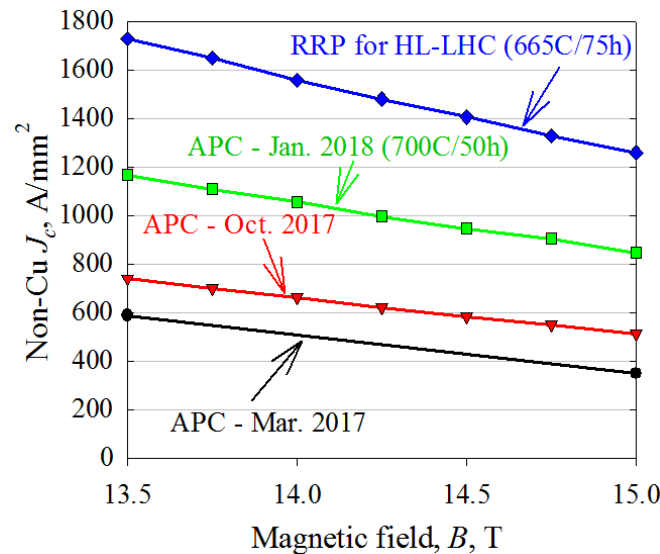
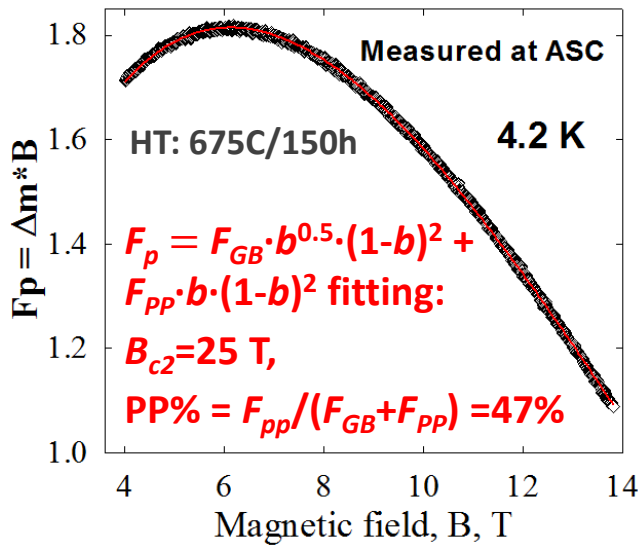
Xingchen Xu

May 9th, 2018

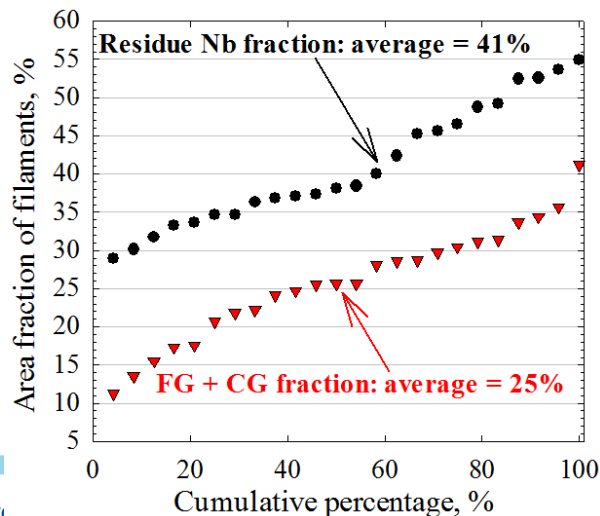
The work is supported by an Fermilab LDRD.

Summary of LTSW talk and what has been done since then

In 2017 a lot of work was done to optimize wire recipe and improve wire quality, and ternary doping was introduced. Below show the results of the wire made just before the LTSW:



Area fraction analysis of the 70C/50h sample: sorted in ascending order.
CG fraction: 5-10% here.



What has been done since LTSW:

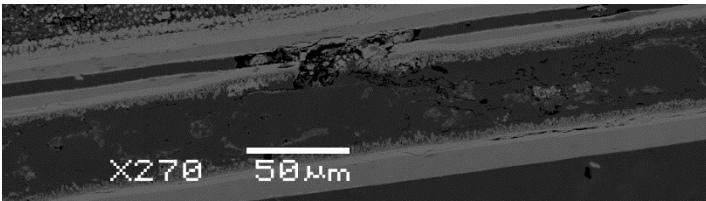
1. Closer analysis of this wire to understand why its non-Cu J_c is not high: bad wire quality issue
2. A non-APC control wire was made to see if the bad wire quality was due to use of APC technique
3. Based on these analyses, new recipe has been determined, and the wire is being made

Why this non-Cu Jc is not high: cause analyses – I

Issue 1: low Nb₃Sn fraction

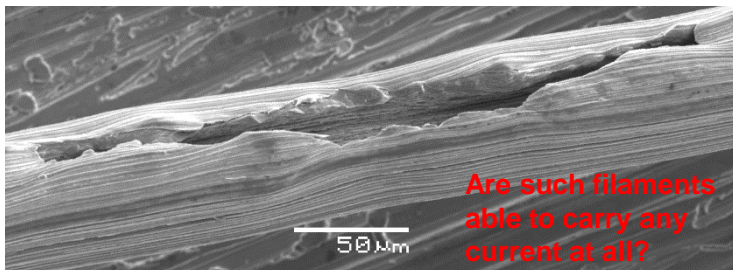
This low Nb₃Sn fraction is not because Sn is insufficient, but is really due to Sn leakage into Cu matrix.

A cause for Sn leakage: improper wire design (too large core):



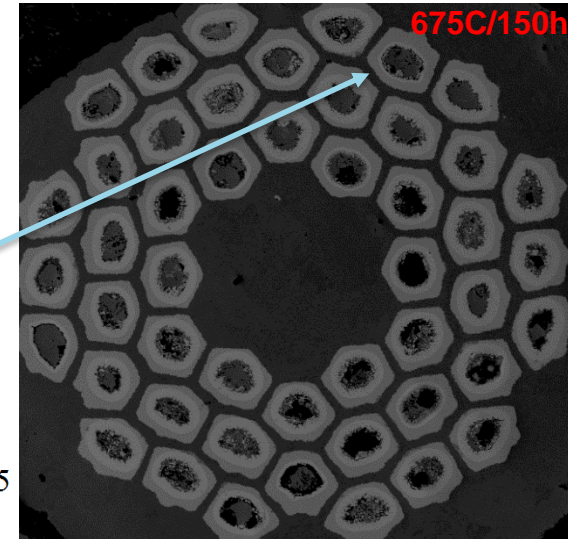
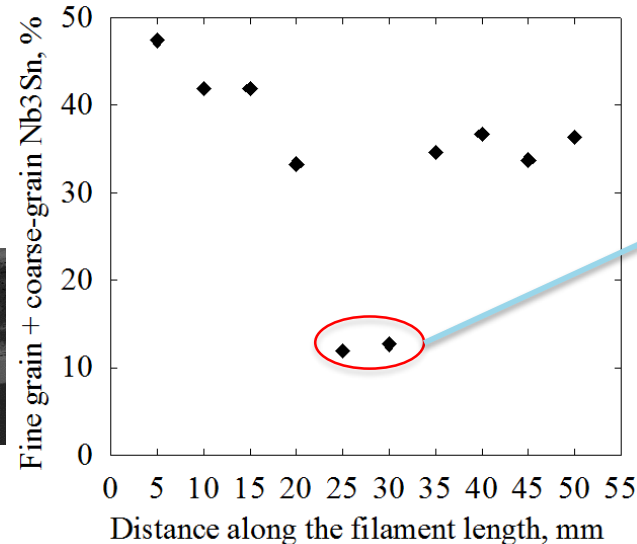
Other causes: see later discussions.

A study: etching the unreacted wire and extracting each filament for SEM:

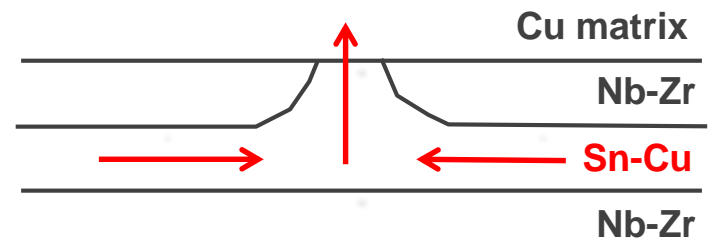


Issue 2: serious non-uniformity (among filaments and in each)

A study: 10 sections polished in a 5-cm long wire, to track the change of Nb₃Sn layer every 5 mm along the length:



Likely cause:
big hard
particles cut
the tube open
during wire
drawing



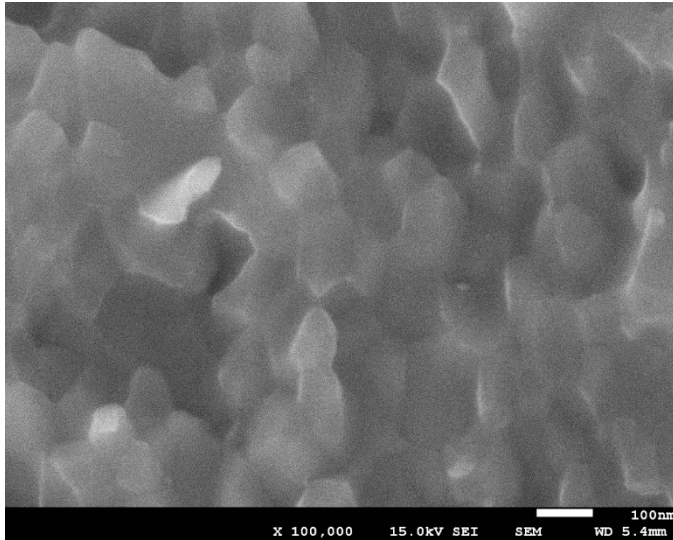
Each leakage spot can cause a long Sn-deficient zone along the length.

Why this non-Cu Jc is not high: cause analyses – II

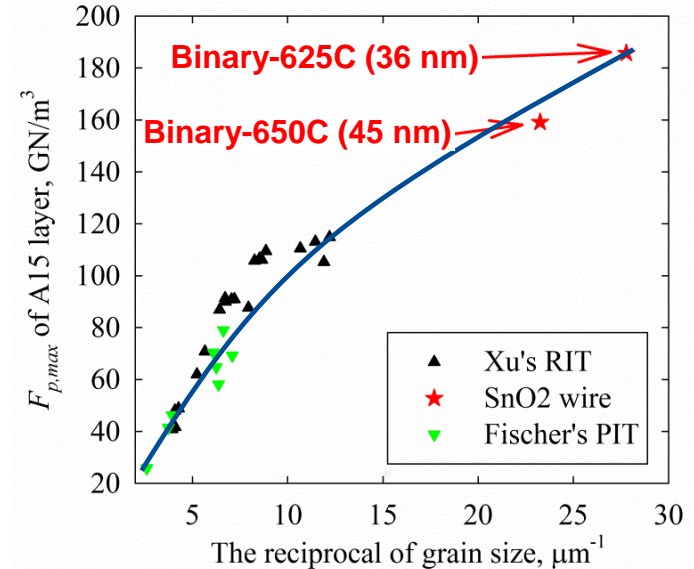
Grain size of the sample is not really small: ~80 nm. Why so big:

(1) This wire was reacted at 700C/50h.

(2) Used Nb-7.5%Ta-0.6%Zr alloy. Lower Zr content → fewer ZrO₂ → less grain refinement

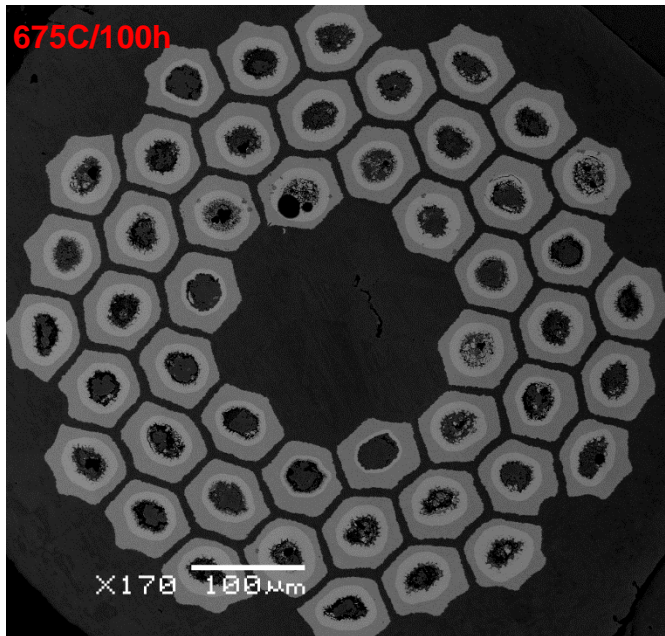


80 nm grain size is smaller than present RRP (120-150 nm), but not small compared with previous 1%Zr wires (binary):



How to solve the Sn leakage issue?

Question: Could this issue be due to the APC technique (i.e., use of Nb-Zr tube or addition of oxide)?
A control wire was made using Nb-7.5%Ta tube and Sn+Cu powders – a totally regular PIT wire.

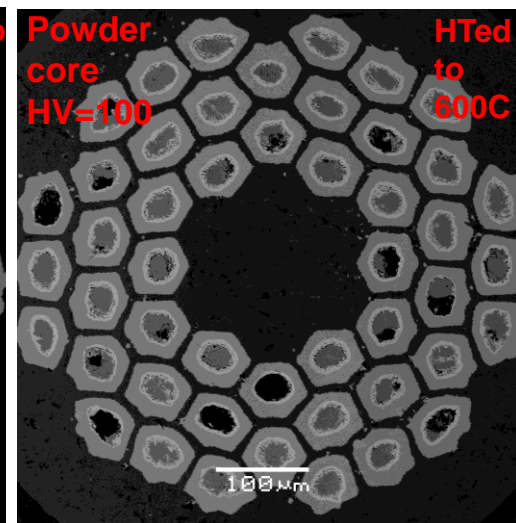
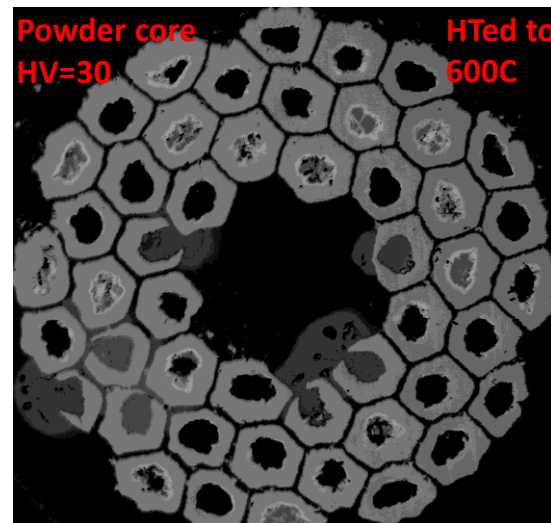


The Sn leakage issue is still there: it is not due to APC technique.

How to solve the Sn leakage issue?

Task 1: improve PIT wire quality during fabrication

- Maybe handling of powders is not proper (e.g., big particles)?
- Maybe powder mixing is not uniform?
- Maybe issue with wire drawing
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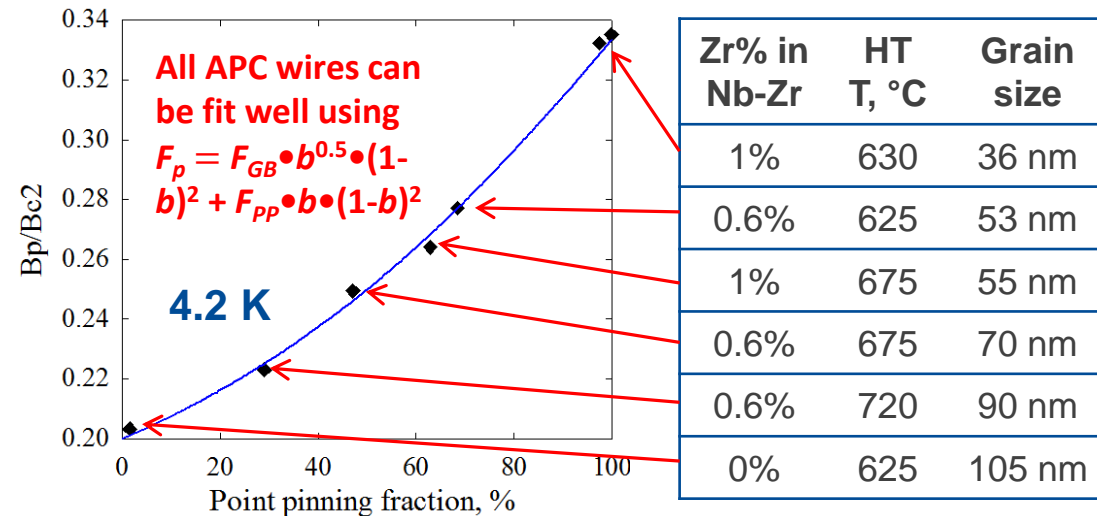


Task 2: optimize wire design and recipe. For example, need to adjust powder recipe to make powder core hard: soft core → eccentric cores → Sn leakage. Another example: too large core → easier for Sn leakage. Optimizing wire design and recipe is a process that takes time.

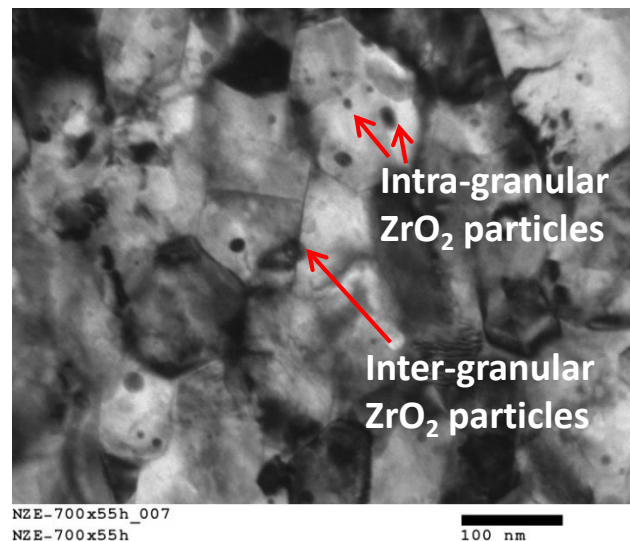
Task 3: need more work to find out if there are other causes.

A discussion about point pinning

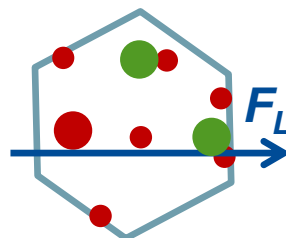
I believed the peak shift in Fp-B curves of APC wires was due to smaller grain size. This is wrong.



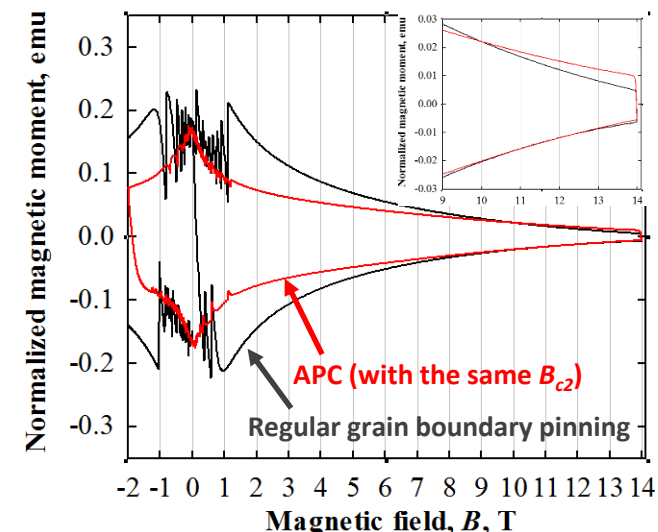
- Even with 90 nm, the PP% is still ~30%, so grain size is irrelevant with peak shift.
- Instead, the point pinners should be ZrO₂ particles (1-10 nm for HT at 700C).
- Total F_p is a sum of GB and ZrO₂ contributions.
- Then why point pinning becomes weaker as HT temperature is higher? Higher HT T or lower Zr% → ZrO₂ particles fewer (sparser) → less effective in point pinning



As point pinning increases from 0 to 100%, F_{GB} drops to 0. How can this happen? Maybe enough ZrO₂ sitting on GBs? If so, F_{pp} should be much stronger than F_{GB} .



Extra benefit: point pinning → Jc-B curve flatter



Summary

1. Despite bad wire quality, the non-Cu J_c of present APC PIT wires is not far from that of RRP now.
2. Room for further improving the non-Cu J_c is huge:
 - 1) This wire: 0.6%Zr + 700 °C → 80 nm GS + 40% PP → doubling of 15 T layer J_c .
Next, 1%Zr + 675 °C → 55 nm + 60% PP → tripling of 15 T layer J_c or more.
Eventually, 1%Zr + 630-640 °C → ~40 nm + 100% PP.
 - 2) This wire: very low Nb₃Sn fraction, with significant non-uniformity also limiting J_c .
Next, need to completely solve Sn leakage issue → to reach 40% uniformly.
3. The Sn leakage issue is due to bad wire quality, which has nothing to do with the APC technique, but most likely due to improper wire design/recipe, powder handling, wire fabrication process, Making high-quality wires requires a wire manufacturer to have a decent technique level of wire fabrication.
4. It was found that the point pinning behavior is caused by ZrO₂ particles. Due to their higher volumetric density, they can provide higher pinning force than grain boundaries. Point pinning makes J_c -B curves flatter, increasing high-field J_c but reduces low-field J_c .
5. Present status of APC: no showstopper, but still needs R&D, needs to make good wires.

Thank you for your attention